



40V N-Channel Trench Power MOSFET

General Description

The SJ40N026 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a wide variety of applications.

Features

- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- Load switch
- Uninterruptible power supply
- Hard switched and high frequency circuits

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(ON_TYP)}$	3.1	m Ω
I_D	146	A
Q_G	95	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJ40N026	SJ40N026	TO-220	Tube	\	\	1000 Pcs

Table 1. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	40	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^\circ\text{C}$)	145	A
	Drain Current-Continuous($T_C=100^\circ\text{C}$)	92	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	580	A
P_D	Maximum Power Dissipation($T_C=25^\circ\text{C}$)	156	W
	Maximum Power Dissipation($T_C=100^\circ\text{C}$)	63	W
E_{AS}	Avalanche energy (Note 2)	702	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.8	$^\circ\text{C}/\text{W}$



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Table 3. Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V, T_J=25^\circ\text{C}$			1	μA
		$V_{DS}=40V, V_{GS}=0V, T_J=125^\circ\text{C}$			100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
g_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=20A$		39		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=20A, T_J=25^\circ\text{C}$		3.1	3.9	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1.0\text{MHz}$		6080		pF
C_{oss}	Output Capacitance			591		pF
C_{rss}	Reverse Transfer Capacitance			456		pF
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0\text{MHz}$		0.7		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=10V, V_{DS}=20V, R_L=1\Omega, R_{GEN}=3\Omega$		25		nS
t_r	Turn-on Rise Time			35		nS
$t_{d(off)}$	Turn-Off Delay Time			105		nS
t_f	Turn-Off Fall Time			35		nS
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=20V, I_D=20A$		95		nC
Q_{gs}	Gate-Source Charge			23		nC
Q_{gd}	Gate-Drain Charge			25		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				146	A
V_{SD}	Forward on Voltage (Note 3)	$V_{GS}=0V, I_S=20A$			1.2	V
t_{rr}	Reverse Recovery Time	$I_F=20A, dI/dt=500A/\mu s$		48		ns
Q_{rr}	Reverse Recovery Charge	$I_F=20A, dI/dt=500A/\mu s$		60		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

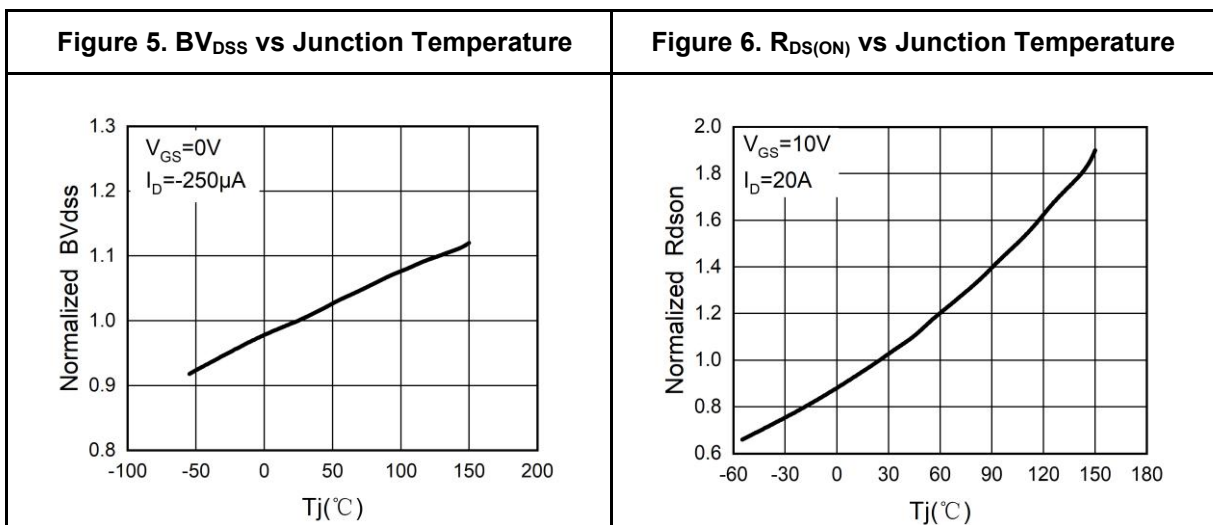
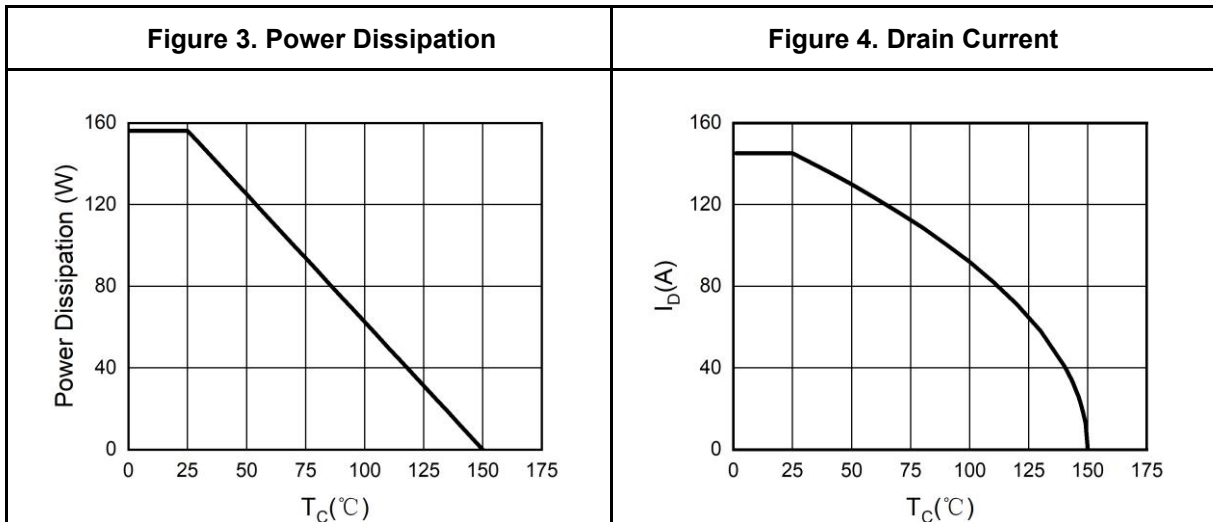
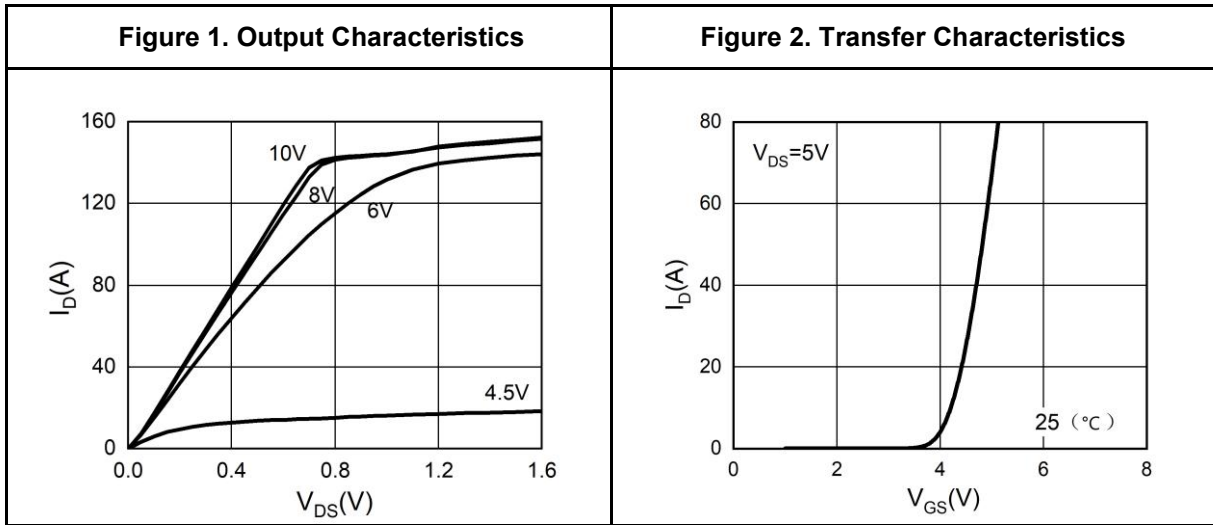
Notes 2.EAS condition: $T_J=25^\circ\text{C}, V_{DD}=40V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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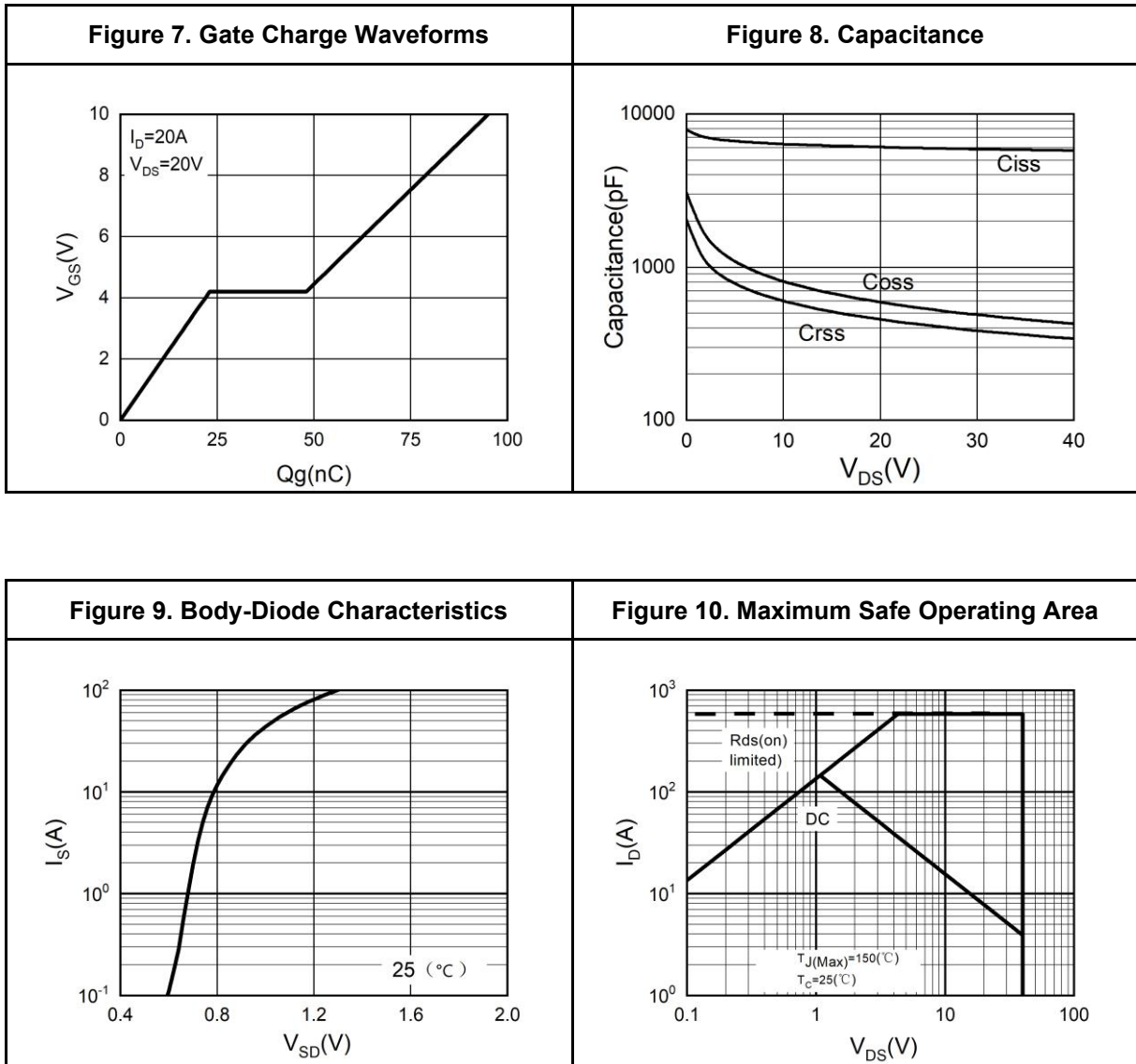
Typical Electrical And Thermal Characteristics (Curves)





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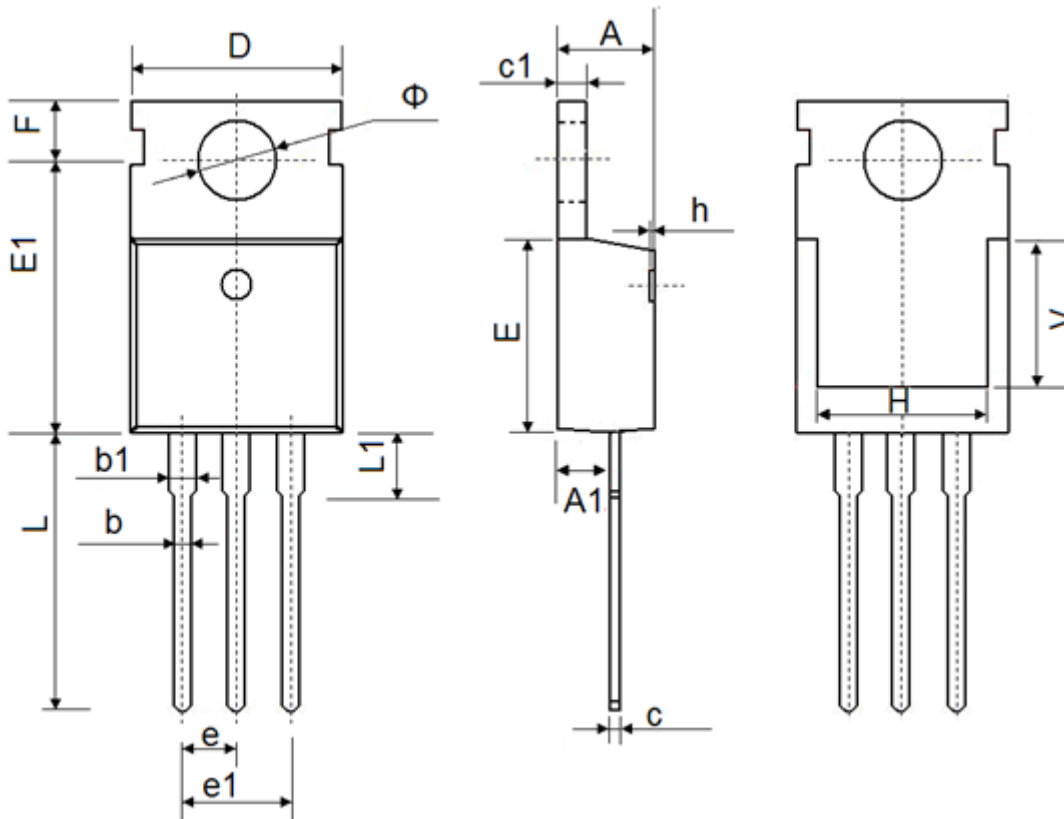
Typical Electrical And Thermal Characteristics (Curves)





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TO-220 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	2.200	2.600	0.087	0.102
b	0.700	0.950	0.028	0.037
b1	1.170	1.410	0.046	0.056
c	0.450	0.650	0.018	0.026
c1	1.200	1.400	0.047	0.055
D	9.600	10.400	0.378	0.409
E	8.8500	9.750	0.348	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.750	14.300	0.502	0.563
L1	2.850	3.950	0.112	0.156
V	7.500 REF.		0.295 REF.	
Φ	3.400	4.000	0.134	0.157



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